2SB936

Preliminary

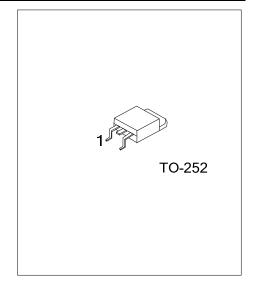
PNP EPITAXIAL SILICON TRANSISTOR

SILICON PNP EPITAXIAL PLANAR TYPE

■ DESCRIPTION

The UTC **2SB936** is a silicon PNP epitaxial planar type, it uses UTC's advanced technology to provide the customers with high DC current gain, low collector to emitter saturation voltage and high switch speed, etc.

The UTC **2SB936** is suitable for small electronic equipment and printed circuit board, etc.



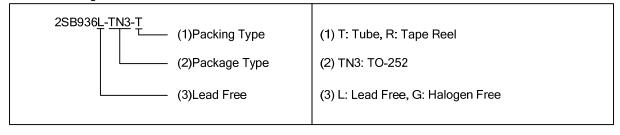
■ FEATURES

- * High DC current gain
- * Low collector to emitter saturation voltage
- * High switch speed

■ ORDERING INFORMATION

Ordering Number		Doolsons	Pin Assignment			Dealine	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SB936L-TN3-T	2SB936G-TN3-T	TO-252	В	С	E	Tube	
2SB936L-TN3-R	2SB936G-TN3-R	TO-252	В	С	E	Tape Reel	

Note: Pin Assignment: B: Base C: Collector E: Emitter



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	-40	V
Collector-Emitter Voltage		$V_{\sf CEO}$	-20	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		Ic	-10	Α
Peak Collector Current		I _{CP}	-20	Α
Callagter Dawer Dissination	T _C =25°C	В	40	W
('Allector Power I liceination F	T _A =25°C	Pc	1.3	W
Junction Temperature		T_J	150	°C
Storage Temperature		T _{STG}	-55 ~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	ВУсво	I _C =-10mA, I _E =0	-40			V
Collector-Emitter Voltage	BV _{CEO}	I _C =-10mA, I _B =0	-20			V
Emitter-Base Breakdown Voltage	ВУево	I _C =-10mA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-40V, I _E =0			-50	μΑ
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5V, I _C =0			-50	μA
DC Current Cain	h _{FE1}	V _{CE} =-2V, I _C =-0.1A	45			
DC Current Gain	h _{FE2}	V _{CE} =-2V, I _C =-3 A	90			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-10A, I _B =-0.33A			-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I _C =-10A, I _B =-0.33A			-1.5	V
Transition Frequency	f _T	V _{CE} =-10V, f=10MHz, I _C =-0.5A		100		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz, I _E =0		400		pF
Turn-On Time	t _{on}			0.1		μs
Storage Time	t _s	I _C =-3A, I _{B1} =-0.1A, I _{B2} =0.1A		0.5		μs
Fall Time	t _r]		0.1		μs

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